

**BEST AVAILABLE COPY****Application No.:  
10/065,003  
Docket NO.:8879-US-PA****Claim Amendment**

**Please amend the claims according to the following listing of claims and substitute it for all prior versions and listings of claims in the application.**

**1. (currently amended) A method of forming holes in a photoresist layer over a substrate, comprising the steps of:**

**exposing the photoresist layer to light through a photomask, wherein the photomask has a plurality of repeated rectangular patterns with inwardly reduced corners having at least a straight cutting side thereon; and**

**developing the photoresist layer to form holes.**

**2. (original) The method of claim 1, wherein after the step of developing the photoresist layer, further includes implanting ions into the substrate using the developed photoresist layer as a mask.**

**3. (currently amended) The method of claim 1, wherein after the step of implanting ions into the substrate, further includes removing the photoresist layer.**

**4. (original) The method of claim 1, wherein the rectangular patterns with inwardly reduced corners on the photomask are suitable for exposing a positive photoresist layer.**

**5. (original) The method of claim 1, wherein the rectangular patterns with inwardly reduced corners comprises a cross-shape pattern.**

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**6. (original) The method of claim 1, wherein the rectangular patterns with inwardly reduced corners comprises a pattern with cut corners.**

**7. (original) A method of forming holes through a cross-shape image exposure, comprising the steps of:**

**forming a photoresist layer over a semiconductor substrate;**

**conducting an exposure using a photomask having a plurality of cross-shape patterns thereon;**

**developing the exposed photoresist layer to form a plurality of holes and exposing a portion of the dielectric layer; and**

**implanting ions into the semiconductor substrate using the developed photoresist layer as a mask.**

**8. (original) The method of claim 7, wherein after the step of implanting ions into the semiconductor substrate, further includes removing the photoresist layer.**

**9. (original) The method of claim 7, wherein the cross-shape patterns on the photomask are suitable for exposing a positive photoresist layer.**

**10. (original) A method of forming contact holes through a cross-shape image exposure, comprising the steps of:**

**forming a semiconductor device over a semiconductor substrate;**

**forming a conductive layer over the semiconductor substrate, wherein the conductive layer is electrically connected to the semiconductor device;**

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**forming a dielectric layer over the semiconductor substrate, wherein the dielectric layer covers the semiconductor device and the conductive layer;**

**forming a photoresist layer over the dielectric layer;**

**conducting a photo-exposure using a photomask having a plurality of cross-shape patterns thereon;**

**developing the photoresist layer to form a plurality of holes; and**

**etching the dielectric layer using the developed photoresist layer as an etching mask to form a plurality of contact holes that exposes the conductive layer.**

**11. (original) The method of claim 10, wherein the cross-shape patterns on the photomask are suitable for exposing a positive photoresist layer.**

**12. (original) The method of claim 10, wherein after the step of etching the dielectric layer, further includes removing the photoresist layer.**

**13. (original) The method of claim 10, wherein after the step of forming a dielectric layer over the semiconductor substrate, further includes planarizing the dielectric layer.**

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